

Tentative Data sheet 1L5ES-A_CP1

Active area: 5,0 x 1,0 mm²

Chip area: 7,2 x 2,0 mm²

Characteristics	Min.	Typ.	Max.	Unit
Position non-linearity		0,05	0,2	% (±)
Detector resistance	40	50	80	kΩ
Leakage current		4	20	nA
Noise current		0,4	1,0	pA/√Hz
Responsivity		3,0		A/W
Capacitance		5	6	pF
Rise time (10%-90%)		0,5	0,8	μs
Bias voltage (reverse)	5	15	30	V
Thermal drift		20	100	ppm/°C

Maximum ratings

Reverse voltage	30	V
Operating temperature	70	°C
Storage temperature	100	°C

Test conditions: Room temperature 23 °C, bias voltage 15V, light source wavelength 940 nm. Position non-linearity and thermal drift are valid within 80 % of the detector length.

Package: 4-pin DIL package, 9,9 x 5,8 mm², with protective window.